INA12x 高精度、低消費電力の計装アンプ

このデバイスには新しいバージョン INA828 が存在します

1 特長

- このデバイスには新しいバージョン INA828 が存在します
- 低いオフセット電圧： 50µV (最大値)
- 低いドリフト係数： 0.5µV/°C (最大値)
- 低い入力バイアス電流： 5nA (最大値)
- 高い CMR： 120dB (最小値)
- ±40V までの入力保護
- 広い電源電圧範囲: ±2.25V～±18V
- 低い静止電流: 700µA
- パッケージ： 8 ピンのプラスチック DIP、SO-8

2 アプリケーション

- ブリッジ・アンプ
- 熱電対アンプ
- RTD センサ・アンプ
- 医療用計測装置
- データ・アクイジション

3 概要

INA128とINA129は、低消費電力の汎用計装アンプで、精度が非常に優れています。多用途の3オペアンプ設計と小さなサイズから、これらのアンプは広範なアプリケーションに理想的です。電流フィードバック入力回路により、高いゲインでも広い帯域幅が得られます (G = 100 で 200kHz)。

単一の外付け抵抗によって、1～10,000の範囲でゲインを設定できます。INA128は業界標準のゲインの式を提供します。INA129のゲインの式はAD620と互換性があります。

INA12xは8ピンのプラスチックDIPおよびSO-8表面実装パッケージで供給され、-40℃～+85℃の温度範囲で動作が規定されています。また、INA128にはデュアル構成のINA2128も用意されています。

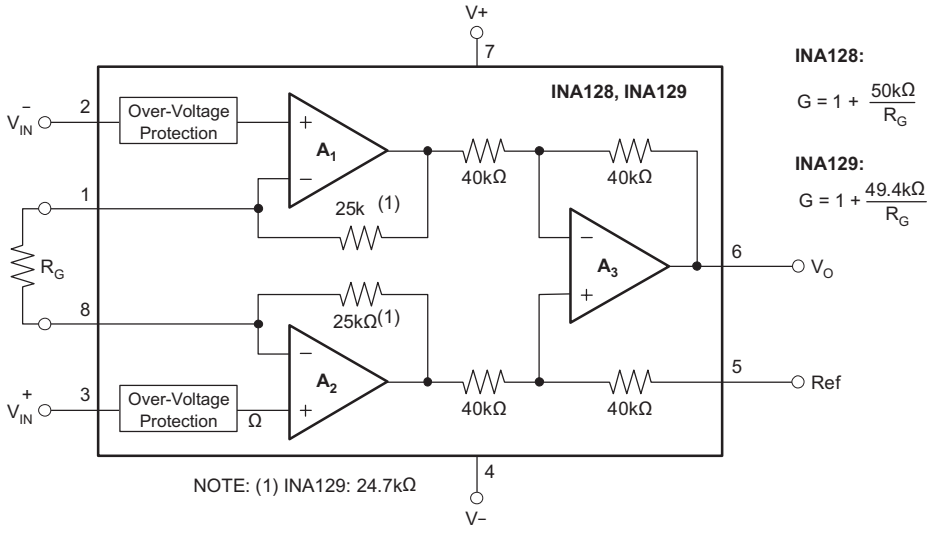
アップグレードされた INA828 は、同じ静止電流で入力バイアス電流 (最大値 0.6nA) とノイズ (7 nV/√Hz) がさらに低減しています。テキサス・インスツルメンツ製の高精度計装アンプのラインナップについては、「*デバイスの比較*」を参照してください。

製品情報(1)

型番	パッケージ	本体サイズ(公称)
INA128、INA129	SOIC (8)	3.91mm×4.90mm
	PDIP (8)	6.35mm×9.81mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にあるパッケージ・オプションについての付録を参照してください。

概略回路図



目次

4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision D (January 2018) から Revision E に変更 **Page**

- 新しいアップグレードされた INA828 の情報を 追加 ... 1
- Added *Device Comparison Table* ... 3

Revision C (October 2015) から Revision D に変更 **Page**

- TI リファレンス・デザインのナビゲータ・アイコンを上端に 追加 ... 1
- Changed "±0.5±0/G" to "±0.5±20/G" in MAX column of Offset voltage RTI vs temperature row of *Electrical Characteristics* ... 5

Revision B (February 2005) から Revision C に変更 **Page**

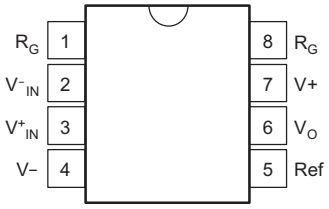
- 「*ESD 定格*」表、「*機能説明*」セクション、「*デバイスの機能モード*」セクション、「*アプリケーションと実装*」セクション、「*電源に関する推奨事項*」セクション、「*レイアウト*」セクション、「*デバイスおよびドキュメントのサポート*」セクション、「*メカニカル、パッケージ、および注文情報*」セクションを追加 ... 1

5 Device Comparison Table

DEVICE	DESCRIPTION	GAIN EQUATION	RG PINS AT PIN
INA828	50-µV Offset, 0.5 µV/°C V_{OS} drift, 7-nV/√Hz Noise, Low-Power, Precision Instrumentation Amplifier	G = 1 + 50 kΩ / RG	1, 8
INA819	35-µV Offset, 0.4 µV/°C V_{OS} drift, 8-nV/√Hz Noise, Low-Power, Precision Instrumentation Amplifier	G = 1 + 50 kΩ / RG	2, 3
INA821	35-µV Offset, 0.4 µV/°C V_{OS} drift, 7-nV/√Hz Noise, High-Bandwidth, Precision Instrumentation Amplifier	G = 1 + 49.4 kΩ / RG	2, 3
INA828	50-µV Offset, 0.5 µV/°C V_{OS} drift, 7-nV/√Hz Noise, Low-Power, Precision Instrumentation Amplifier	G = 1 + 50 kΩ / RG	1, 8
INA333	25-µV V_{OS}, 0.1 µV/°C V_{OS} drift, 1.8-V to 5-V, RRO, 50-µA I_Q, chopper-stabilized INA	G = 1 + 100 kΩ / RG	1, 8
PGA280	20-mV to ±10-V programmable gain IA with 3-V or 5-V differential output; analog supply up to ±18 V	digital programmable	N/A
INA159	G = 0.2 V differential amplifier for ±10-V to 3-V and 5-V conversion	G = 0.2 V/V	N/A
PGA112	Precision programmable gain op amp with SPI	digital programmable	N/A

6 Pin Configuration and Functions

D and P Packages
8-Pin SOIC and PDIP
Top View



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
REF	5	I	Reference input. This pin must be driven by low impedance or connected to ground.
R_G	1,8	—	Gain setting pin. For gains greater than 1, place a gain resistor between pin 1 and pin 8.
V-	4	—	Negative supply
V+	7	—	Positive supply
V_{IN-}	2	I	Negative input
V_{IN+}	3	I	Positive input
V_O	6	I	Output

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

	MIN	MAX	UNIT
Supply voltage		±18	V
Analog input voltage		±40	V
Output short circuit (to ground)		continuous	
Operating temperature	–40	125	°C
Junction temperature		150	°C
Lead temperature (soldering, 10 seconds)		300	°C
Storage temperature, T_{stg}	–55	125	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±50	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	NOM	MAX	UNIT
V power supply	±2.25	±15	±18	V
Input common-mode voltage range for V_O = 0	V – 2 V		V + –2 V	
T_A operating temperature INA128-HT	–55		175	°C
T_A operating temperature INA129-HT	–55		210	°C

7.4 Thermal Information

THERMAL METRIC(1)		INA12x		UNIT
		D (SOIC)	P (PDIP)	
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	110	46.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	57	34.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	54	23.4	°C/W
ψ_{JT}	Junction-to-top characterization parameter	11	11.3	°C/W
ψ_{JB}	Junction-to-board characterization parameter	53	23.2	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

7.5 Electrical Characteristics

at T_A = 25°C, V_S = ±15 V, and R_L = 10 kΩ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
INPUT							
Offset voltage, RTI	Initial	T_A = 25°C	INA128P, U INA129P, U		±10±100/G	±50±500/G	µV
			INA128PA, UA INA129PA, UA		±25±100/G	±125±1000/G	
	vs temperature	T_A = T_{MIN} to T_{MAX}	INA128P, U INA129P, U		±0.2±2/G	±0.5±20/G	µV/°C
			INA128PA, UA INA129PA, UA		±0.2±5/G	±1±20/G	
	vs power supply	V_S = ±2.25 V to ±18 V	INA128P, U INA129P, U		±0.2±20/G	±1±100/G	µV/V
			INA128PA, UA INA129PA, UA			±2±200/G	
	Long-term stability				±0.1±3/g		µV/mo
Impedance	Differential				10^{10} || 2		Ω || pF
	Common mode				10^{11} || 9		
Common-mode voltage range(1)		V_O = 0 V		(V+) - 2	(V+) - 1.4		V
				(V…) + 2	(V–) + 1.7		
Safe input voltage						±40	V

(1) Input common-mode range varies with output voltage; see Typical Characteristics.

Electrical Characteristics (continued)

at T_A = 25°C, V_S = ±15 V, and R_L = 10 kΩ (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
Common-mode rejection		V_{CM} = ±13 V, ΔR_S = 1 kΩ	G = 1	INA128P, U INA129P, U	80	86		dB
				INA128PA, UA INA129PA, UA	73			
			G = 10	INA128P, U INA129P, U	100	106		
				INA128PA, UA INA129PA, UA	93			
			G = 100	INA128P, U INA129P, U	120	125		
				INA128PA, UA INA129PA, UA	110			
			G = 1000	INA128P, U INA129P, U	120	130		
				INA128PA, UA INA129PA, UA	110			
Bias current		INA128P, U INA129P, U				±2	±5	nA
		INA128PA, UA INA129PA, UA					±10	
Bias current vs temperature						±30		pA/°C
Offset current		INA128P, U INA129P, U				±1	±5	nA
		INA128PA, UA INA129PA, UA					±10	
Offset current vs temperature						±30		pA/°C
Noise voltage, RTI	f = 10 Hz	G = 1000, R_S = 0Ω				10		nV/√Hz
	f = 100 Hz					8		
	f = 1 kHz					8		
	f_B = 0.1 Hz to 10 Hz					0.2		μV_{PP}
Noise current	f = 10 Hz					0.9		pA/√Hz
	f = 1 kHz					0.3		
	F_B = 0.1 Hz to 10 Hz					30		pA_{PP}
GAIN[2]								
Gain equation	INA128					1 + (50 kΩ/R_G)		V/V
	INA129					1 + (49.4 kΩ/R_G)		
Range of gain					1		10000	V/V
Gain error		G = 1		INA128P, U INA129P, U		±0.01%	±0.024%	
				INA128PA, UA INA129PA, UA			±0.01%	
		G = 10		INA128P, U INA129P, U		±0.02%	±0.4%	
				INA128PA, UA INA129PA, UA			±0.5%	
		G = 100		INA128P, U INA129P, U		±0.05%	±0.5%	
				INA128PA, UA INA129PA, UA			±0.7%	
		G = 1000		INA128P, U INA129P, U		±0.5%	±1%	
				INA128PA, UA INA129PA, UA			±2%	

(2) Nonlinearity measurements in G = 1000 are dominated by noise. Typical non-linearity is ±0.001%.

Electrical Characteristics (continued)

at T_A = 25°C, V_S = ±15 V, and R_L = 10 kΩ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
Gain vs temperature(3)		G = 1			±1	±10	ppm/°C
		50-kΩ (or 49.4-kΩ) Resistance(3)(4)			±25	±100	
Nonlinearity		V_O = ±13.6 V, G = 1	INA128P, U INA129P, U		±0.0001	±0.001	% of FSR
			INA128PA, UA INA129PA, UA			±0.002	
		G = 10	INA128P, U INA129P, U		±0.0003	±0.002	
			INA128PA, UA INA129PA, UA			±0.004	
		G = 100	INA128P, U INA129P, U		±0.0005	±0.002	
			INA128PA, UA INA129PA, UA			±0.004	
		G = 1000			±0.001	/>	
OUTPUT(2)							
Voltage	Positive	R_L = 10 kΩ		(V+) – 1.4	(V+) – 0.9		V
	Negative	R_L = 10 kΩ		(V–) + 1.4	(V–) + 0.8		
Load capacitance stability					1000		pF
Short-circuit current					6/–15		mA
FREQUENCY RESPONSE							
Bandwidth, –3 dB		G = 1			1.3		MHz
		G = 10			700		kHz
		G = 100			200		
		G = 1000			20		
Slew rate		V_O = ±10 V, G = 10			4		V/µs
Settling time, 0.01%		G = 1			7		µs
		G = 10			7		
		G = 100			9		
		G = 1000			80		
Overload recovery		50% overdrive			4		µs
POWER SUPPLY							
Voltage range				±2.25	±15	±18	V
Current, total		V_{IN} = 0 V			±700	±750	µA
TEMPERATURE RANGE							
Specification				–40		85	°C
Operating				–40		125	°C

(3) Specified by wafer test.
(4) Temperature coefficient of the 50 kΩ (or 49.4 kΩ) term in the gain equation.

7.6 Typical Characteristics

at T_A = 25°C and V_S = ±15 V (unless otherwise noted)

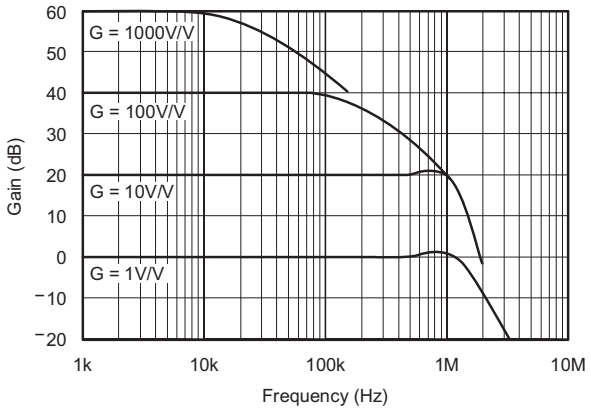


Figure 1. Gain vs Frequency

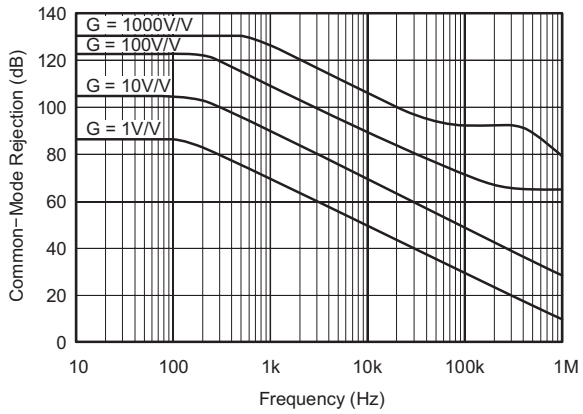


Figure 2. Common-Mode Rejection vs Frequency

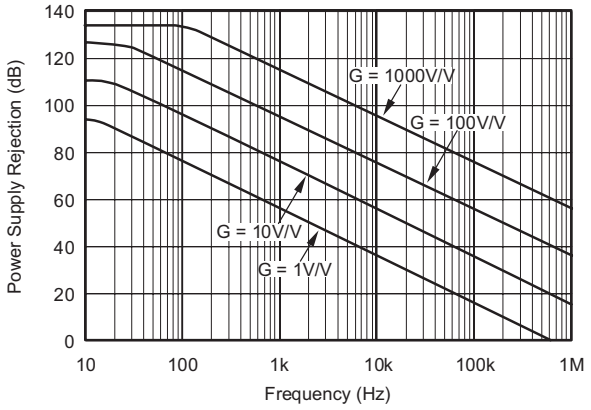


Figure 3. Positive Power Supply Rejection vs Frequency

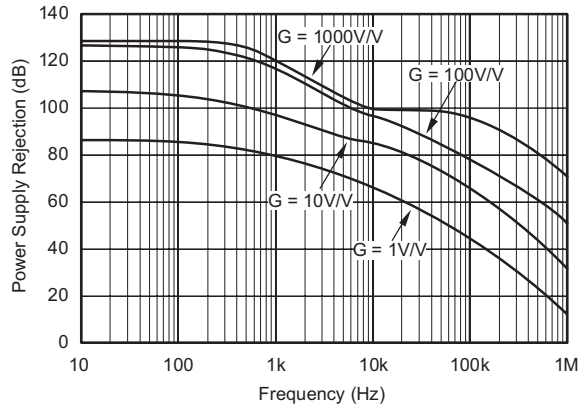


Figure 4. Negative Power Supply Rejection vs Frequency

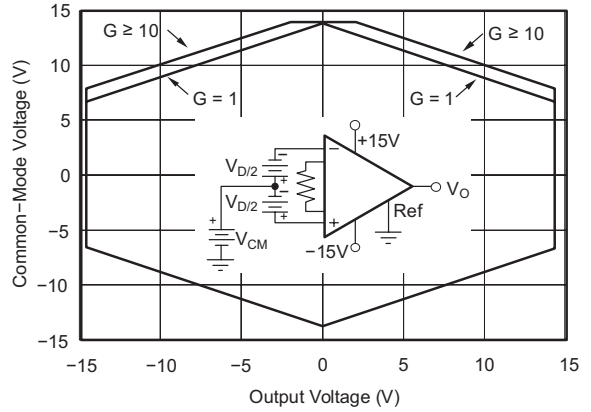


Figure 5. Input Common-Mode Range vs Output Voltage, V_S = ±15 V

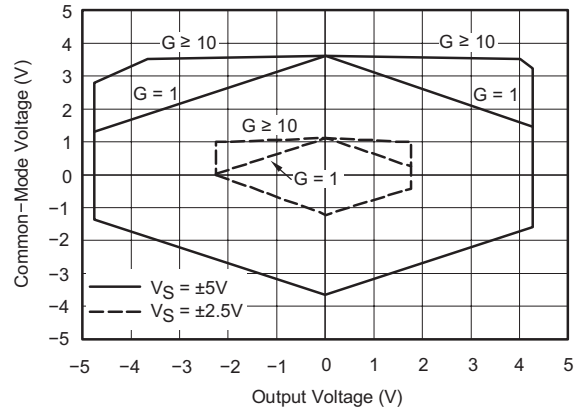


Figure 6. Input Common-Mode Range vs Output Voltage, V_S = ±5 V, ±2.5 V

Typical Characteristics (continued)

at T_A = 25°C and V_S = ±15 V (unless otherwise noted)

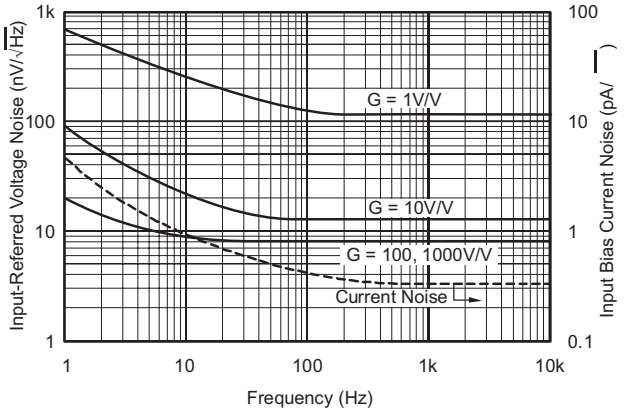


Figure 7. Input-Referred Noise vs Frequency

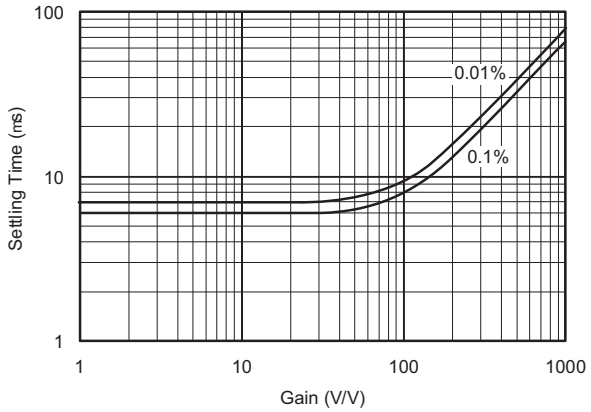


Figure 8. Settling Time vs Gain

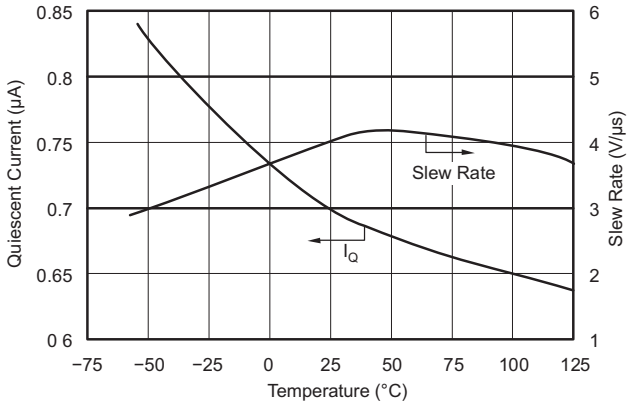


Figure 9. Quiescent Current and Slew Rate vs Temperature

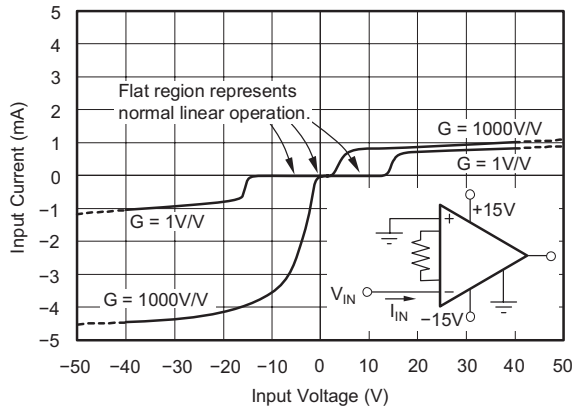


Figure 10. Input Overvoltage V/I Characteristics

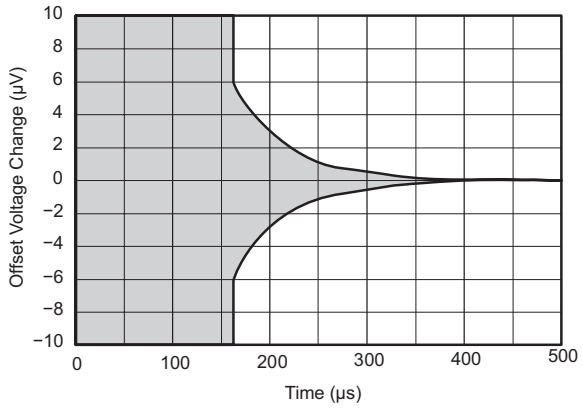


Figure 11. Input Offset Voltage Warm-Up

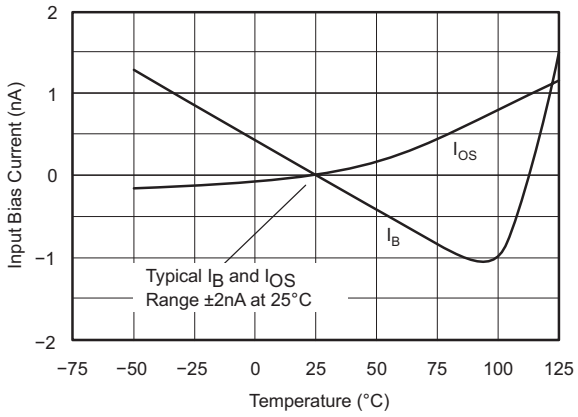


Figure 12. Input Bias Current vs Temperature

Typical Characteristics (continued)

at T_A = 25°C and V_S = ±15 V (unless otherwise noted)

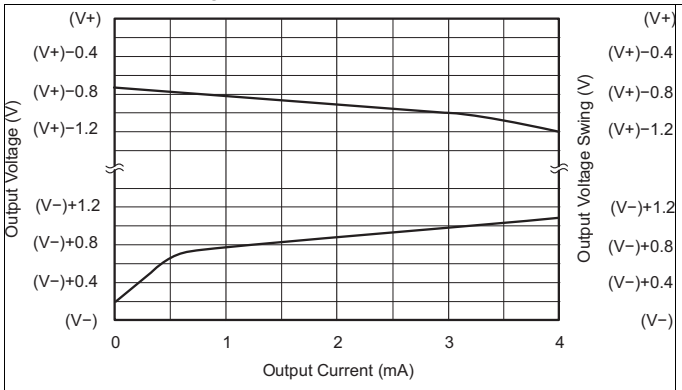


Figure 13. Output Voltage Swing vs Output Current

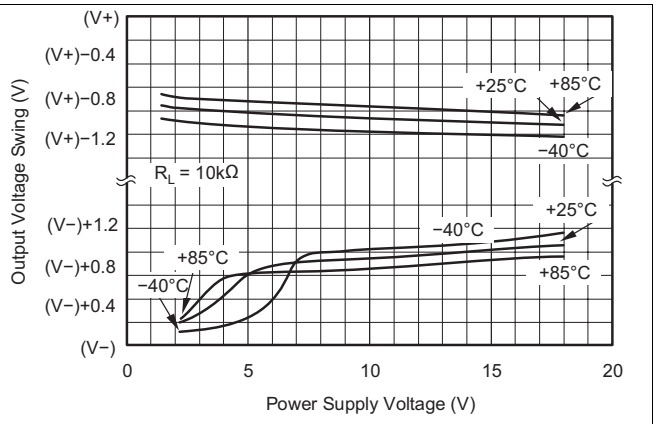


Figure 14. Output Voltage Swing vs Power Supply Voltage

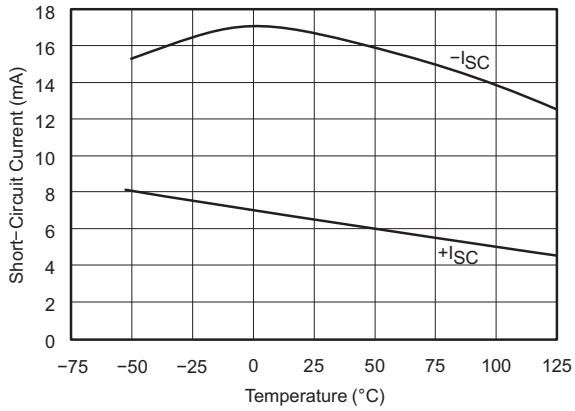


Figure 15. Short Circuit Output Current vs Temperature

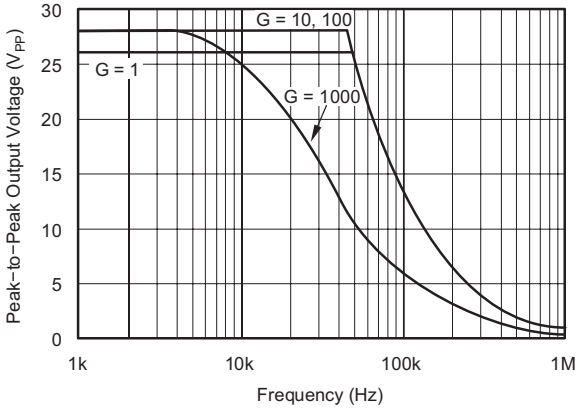


Figure 16. Maximum Output Voltage vs Frequency

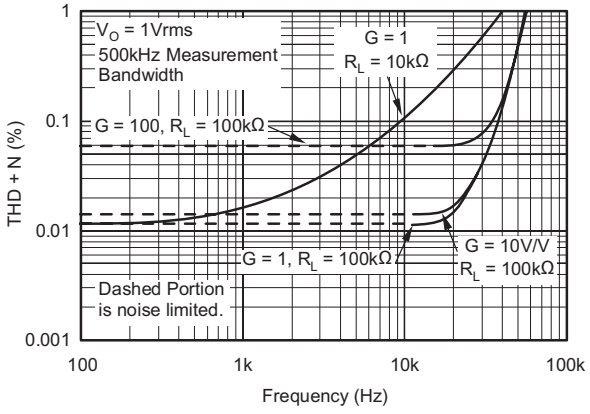


Figure 17. Total Harmonic Distortion + Noise vs Frequency

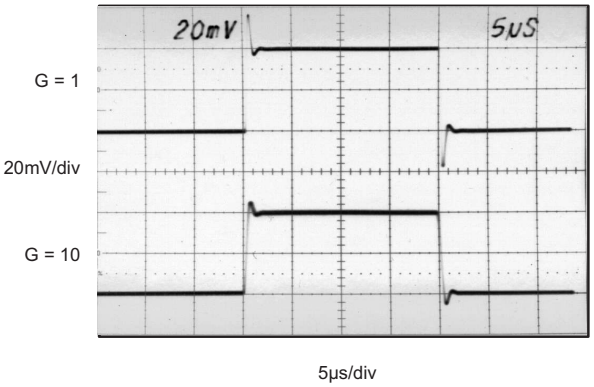


Figure 18. Small Signal (G = 1, 10)

Typical Characteristics (continued)

at T_A = 25°C and V_S = ±15 V (unless otherwise noted)

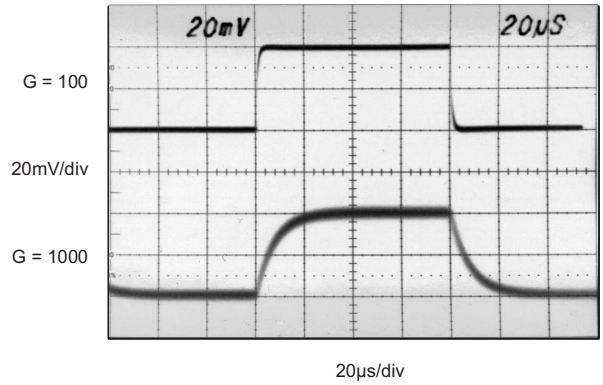


Figure 19. Small Signal (G = 100, 1000)

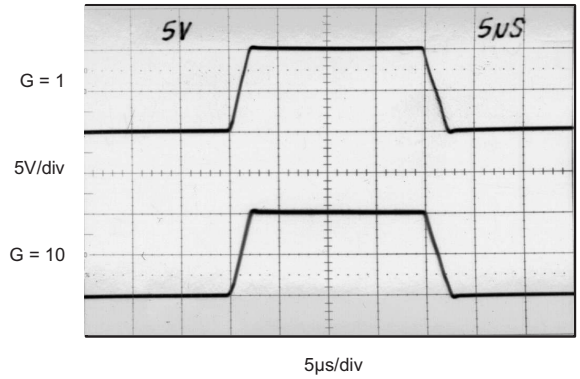


Figure 20. Large Signal (G = 1, 10)

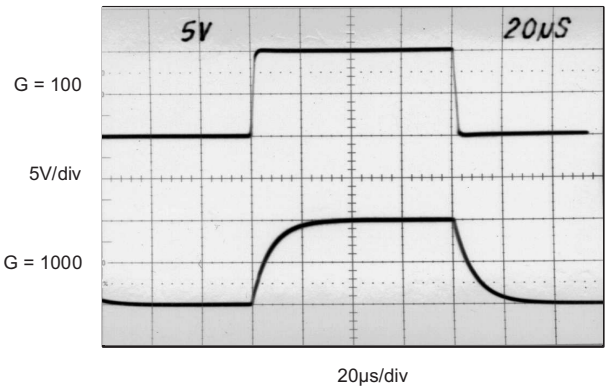


Figure 21. Large Signal (G = 100, 1000)

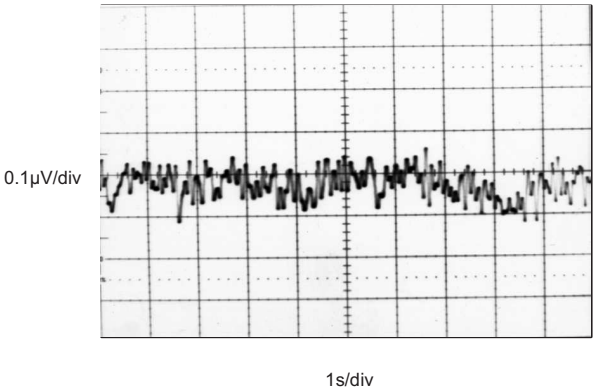


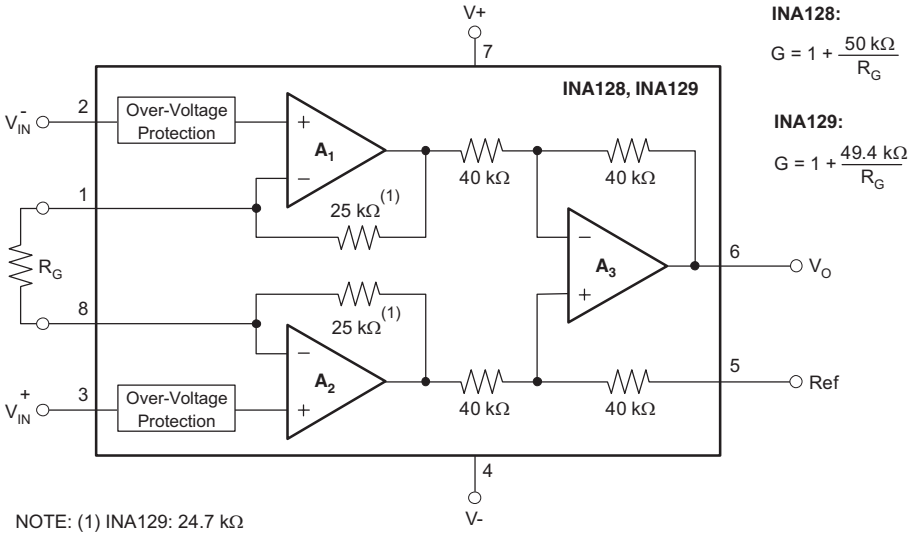
Figure 22. Voltage Noise 0.1 to 10-Hz Input-Referred, G ≥ 100

8 Detailed Description

8.1 Overview

The INA12x instrumentation amplifier is a type of differential amplifier that has been outfitted with input protection circuit and input buffer amplifiers, which eliminate the need for input impedance matching and make the amplifier particularly suitable for use in measurement and test equipment. Additional characteristics of the INA128 include a very low DC offset, low drift, low noise, very high open-loop gain, very high common-mode rejection ratio, and very high input impedances. The INA12x is used where great accuracy and stability of the circuit both short and long term are required.

8.2 Functional Block Diagram



8.3 Feature Description

The INA12x devices are low power, general-purpose instrumentation amplifiers offering excellent accuracy. The versatile three-operational-amplifier design and small size make the amplifiers ideal for a wide range of applications. Current-feedback input circuitry provides wide bandwidth, even at high gain. A single external resistor sets any gain from 1 to 10,000. The INA128 is laser trimmed for very low offset voltage (25 μV typical) and high common-mode rejection (93 dB at G ≥ 100). These devices operate with power supplies as low as ±2.25 V, and quiescent current of 2 mA, typically. The internal input protection can withstand up to ±40 V without damage.

8.4 Device Functional Modes

8.4.1 Noise Performance

The INA12x provides very low noise in most applications. Low-frequency noise is approximately 0.2 μV_{PP} measured from 0.1 to 10 Hz (G ≥ 100). This provides dramatically improved noise when compared to state-of-the-art chopper-stabilized amplifiers.

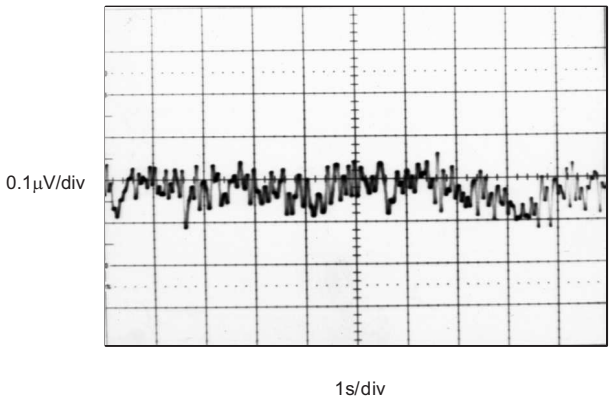


Figure 23. 0.1-Hz to 10-Hz Input-Referred Voltage Noise

8.4.2 Input Common-Mode Range

The linear input voltage range of the input circuitry of the INA12x is from approximately 1.4 V below the positive supply voltage to 1.7 V above the negative supply. As a differential input voltage causes the output voltage increase, however, the linear input range is limited by the output voltage swing of amplifiers A_1 and A_2. Thus the linear common-mode input range is related to the output voltage of the complete amplifier. This behavior also depends on supply voltage (see performance curve Figure 6).

Input-overload can produce an output voltage that appears normal. For example, if an input overload condition drives both input amplifiers to their positive output swing limit, the difference voltage measured by the output amplifier will be near zero. The output of A_3 will be near 0 V even though both inputs are overloaded.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The INA12x measures small differential voltage with high common-mode voltage developed between the noninverting and inverting input. The high-input voltage protection circuit in conjunction with high input impedance make the INA12x suitable for a wide range of applications. The ability to set the reference pin to adjust the functionality of the output signal offers additional flexibility that is practical for multiple configurations.

9.2 Typical Application

Figure 24 shows the basic connections required for operation of the INA12x. Applications with noisy or high impedance power supplies may require decoupling capacitors close to the device pins as shown. The output is referred to the output reference (Ref) terminal which is normally grounded. This must be a low-impedance connection to assure good common-mode rejection. A resistance of 8 Ω in series with the Ref pin will cause a typical device to degrade to approximately 80dB CMR (G = 1).

INA128: $G = 1 + \frac{50k}{R_G}$ **INA129:** $G = 1 + \frac{49.4k}{R_G}$

DESIRED GAIN (V/V)	INA128 R_G (Ω)	INA128 NEAREST 1% R_G (Ω)	INA129 R_G (Ω)	INA129 NEAREST 1% R_G (Ω
1	NC	NC	NC	NC
2	50.00k	49.9k	49.4k	49.9k
5	12.50k	12.4k	12.35k	12.4k
10	5.556k	5.62k	5489	5.49k
20	2.632k	2.61k	2600	2.61k
50	1.02k	1.02k	1008	1k
100	505.1	511	499	499
200	251.3	249	248	249
500	100.2	100	99	100
1000	50.05	49.9	49.5	49.9
2000	25.01	24.9	24.7	24.9
5000	10.00	10	9.88	9.76
10000	5.001	4.99	4.94	4.87

NC: No Connection

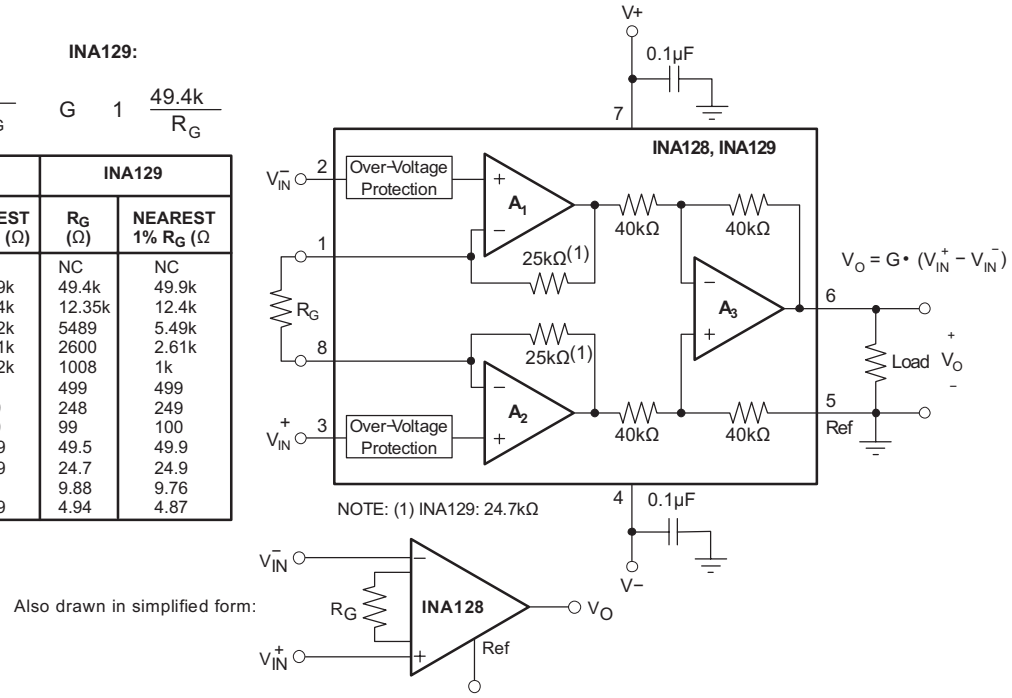


Figure 24. Basic Connections

Typical Application (continued)

9.2.1 Design Requirements

The device can be configured to monitor the input differential voltage when the gain of the input signal is set by the external resistor R_G. The output signal references to the Ref pin. The most common application is where the output is referenced to ground when no input signal is present by connecting the Ref pin to ground, as Figure 24 shows. When the input signal increases, the output voltage at the OUT pin increases, too.

9.2.2 Detailed Design Procedure

9.2.2.1 Setting the Gain

Gain is set by connecting a single external resistor, R_G, connected between pins 1 and 8:

$$\text{INA128: } g = 1 + 50\ \text{k}\Omega/R_G \quad (1)$$

Commonly used gains and resistor values are shown in Figure 24.

The 50-kΩ term in Equation 1 comes from the sum of the two internal feedback resistors of A_1 and A_2. These on-chip metal film resistors are laser-trimmed to accurate absolute values. The accuracy and temperature coefficient of these internal resistors are included in the gain accuracy and drift specifications of the INA128.

The stability and temperature drift of the external gain setting resistor, R_G, also affects gain. The contribution of R_G to gain accuracy and drift can be directly inferred from Equation 1. Low resistor values required for high gain can make wiring resistance important. Sockets add to the wiring resistance, which contributes additional gain error (possibly an unstable gain error) in gains of approximately 100 or greater.

9.2.2.2 Dynamic Performance

The typical performance curve *Figure 1* shows that, despite its low quiescent current, the INA12x achieves wide bandwidth even at high gain. This is due to the current-feedback topology of the input stage circuitry. Settling time also remains excellent at high gain.

9.2.2.3 Offset Trimming

The INA12x is laser-trimmed for low-offset voltage and offset voltage drift. Most applications require no external offset adjustment. Figure 25 shows an optional circuit for trimming the output offset voltage. The voltage applied to the Ref terminal is summed with the output. The op amp buffer provides low impedance at the Ref terminal to preserve good common-mode rejection.

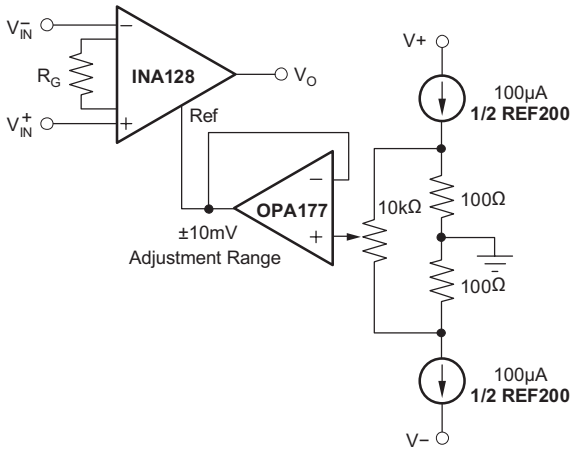


Figure 25. Optional Trimming of Output Offset Voltage

9.2.2.4 Input Bias Current Return Path

The input impedance of the INA12x is extremely high: approximately 10^{10} Ω. However, a path must be provided for the input bias current of both inputs. This input bias current is approximately ±2 nA. High input impedance means that this input bias current changes very little with varying input voltage.

Typical Application (continued)

Input circuitry must provide a path for this input bias current for proper operation. Figure 26 shows various provisions for an input bias current path. Without a bias current path, the inputs will float to a potential which exceeds the common-mode range, and the input amplifiers will saturate.

If the differential source resistance is low, the bias current return path can be connected to one input (see the thermocouple example in Figure 26). With higher source impedance, using two equal resistors provides a balanced input, with possible advantages of lower input offset voltage due to bias current and better high-frequency common-mode rejection.

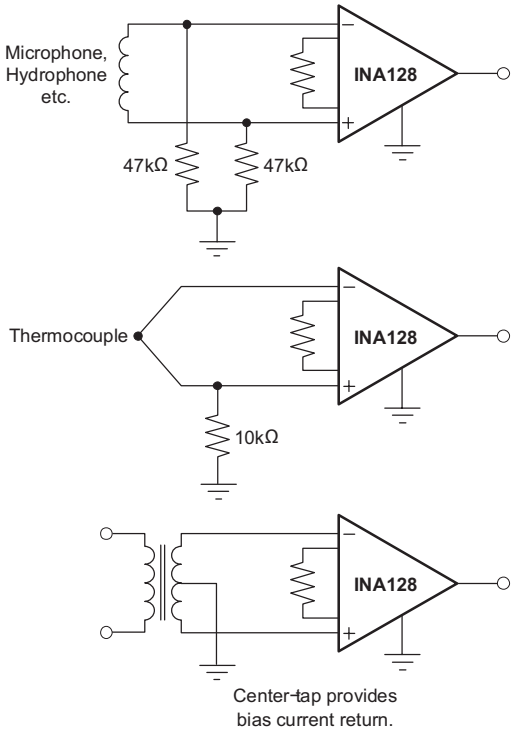
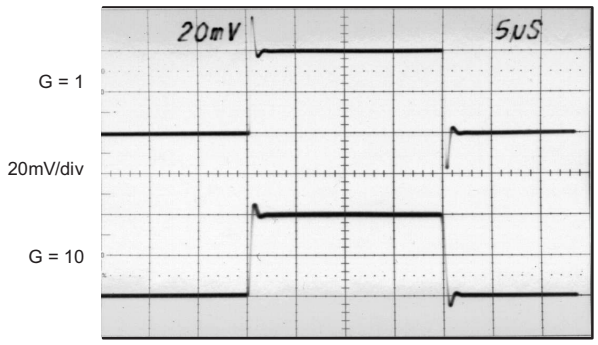


Figure 26. Providing an Input Common-Mode Current Path

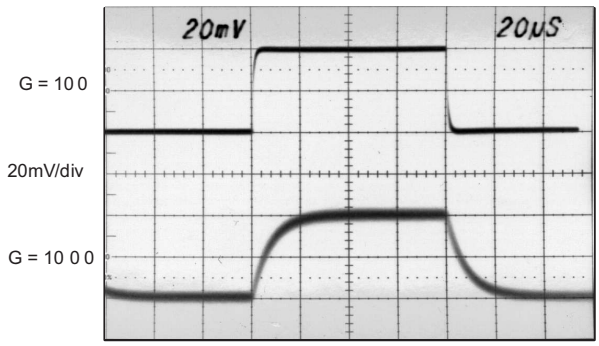
Typical Application (continued)

9.2.3 Application Curves



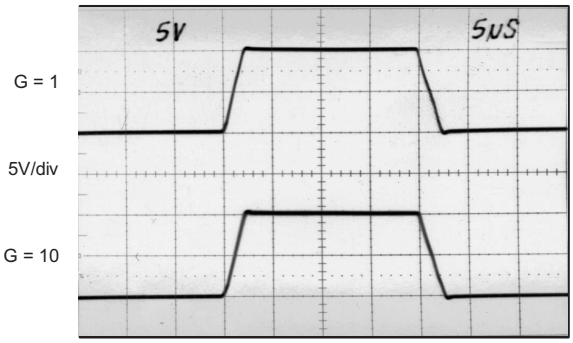
5µs/div
G = 1, 10

Figure 27. Small Signal



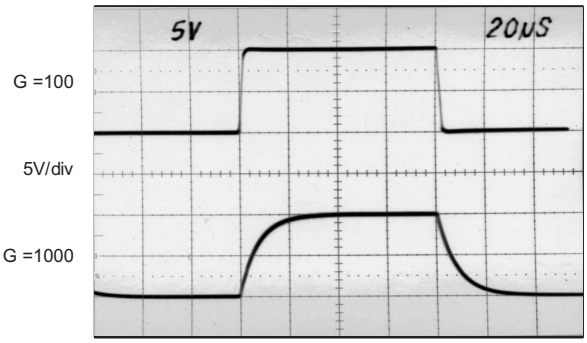
20µs/div
G = 100, 1000

Figure 28. Small Signal



5µs/div
G = 1, 10

Figure 29. Large Signal



20µs/div
G = 100, 1000

Figure 30. Large Signal

10 Power Supply Recommendations

The minimum power supply voltage for INA12x is ±2.25 V and the maximum power supply voltage is ±18 V. This minimum and maximum range covers a wide range of power supplies; but for optimum performance, ±15 V is recommended. TI recommends adding a bypass capacitor at the input to compensate for the layout and power supply source impedance.

10.1 Low Voltage Operation

The INA12x can be operated on power supplies as low as ±2.25 V. Performance remains excellent with power supplies ranging from ±2.25 V to ±18 V. Most parameters vary only slightly throughout this supply voltage range—see *Typical Characteristics*.

Operation at very low supply voltage requires careful attention to assure that the input voltages remain within their linear range. Voltage swing requirements of internal nodes limit the input common-mode range with low power supply voltage. Figure 6 shows the range of linear operation for ±15-V, ±5-V, and ±2.5-V supplies.

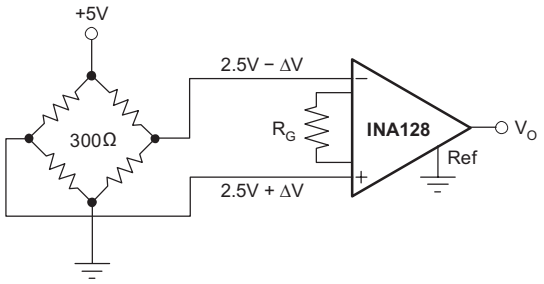


Figure 31. Bridge Amplifier

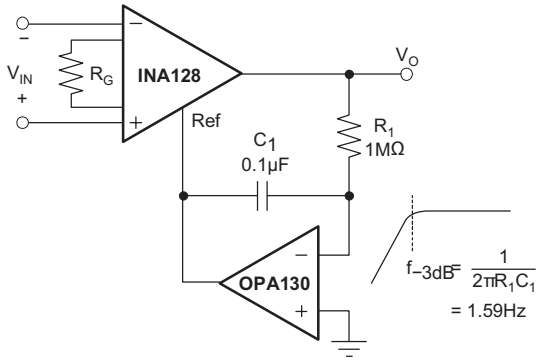
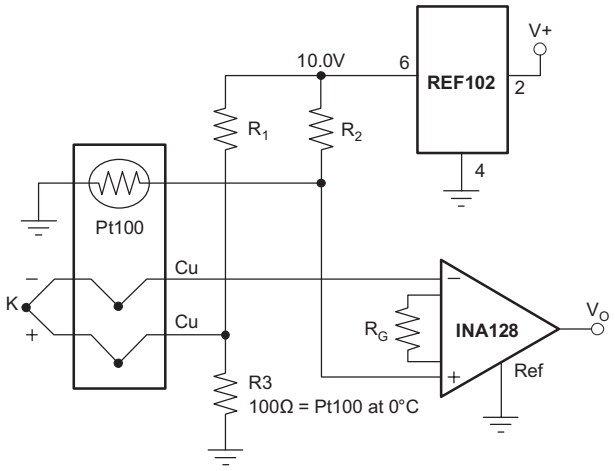


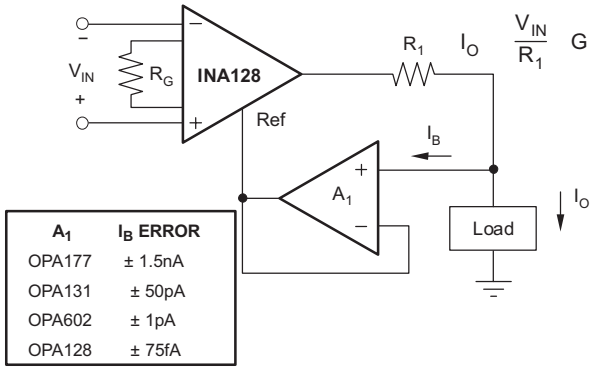
Figure 32. AC-Coupled Instrumentation Amplifier

Low Voltage Operation (continued)



ISA TYPE	MATERIAL	SEEBECK COEFFICIENT (C)	R1, R2
E	+ Chromel − Constantan	58.5	66.5kΩ
J	+ Iron − Constantan	50.2	76.8kΩ
K	+ Chromel − Alumel	39.4	97.6kΩ
T	+ Copper − Constantan	38.0	102kΩ

Figure 33. Thermocouple Amplifier With RTD Cold-Junction Compensation



A1	IB ERROR
OPA177	± 1.5nA
OPA131	± 50pA
OPA602	± 1pA
OPA128	± 75fA

Figure 34. Differential Voltage to Current Converter

Low Voltage Operation (continued)

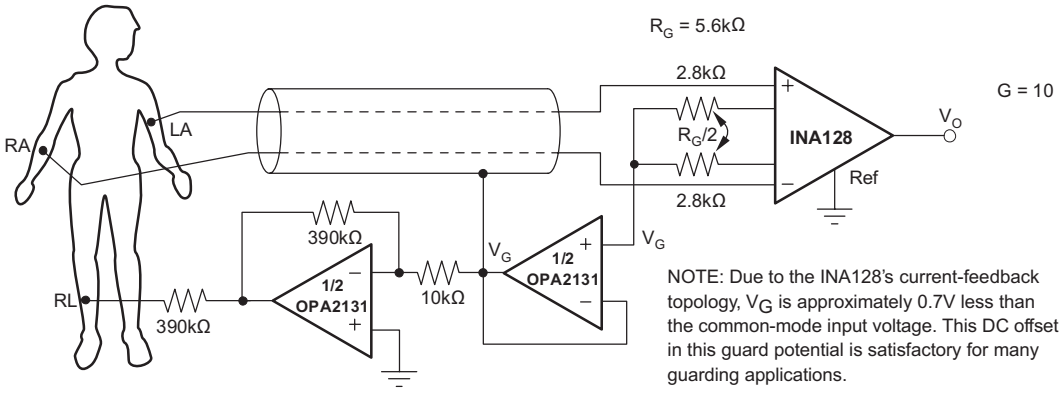


Figure 35. ECG Amplifier With Right-Leg Drive

11 Layout

11.1 Layout Guidelines

Place the power-supply bypass capacitor as closely as possible to the supply and ground pins. The recommended value of this bypass capacitor is 0.1 μF to 1 μF. If necessary, additional decoupling capacitance can be added to compensate for noisy or high-impedance power supplies. These decoupling capacitors must be placed between the power supply and INA12x devices.

The gain resistor must be placed close to pin 1 and pin 8. This placement limits the layout loop and minimizes any noise coupling into the part.

11.2 Layout Example

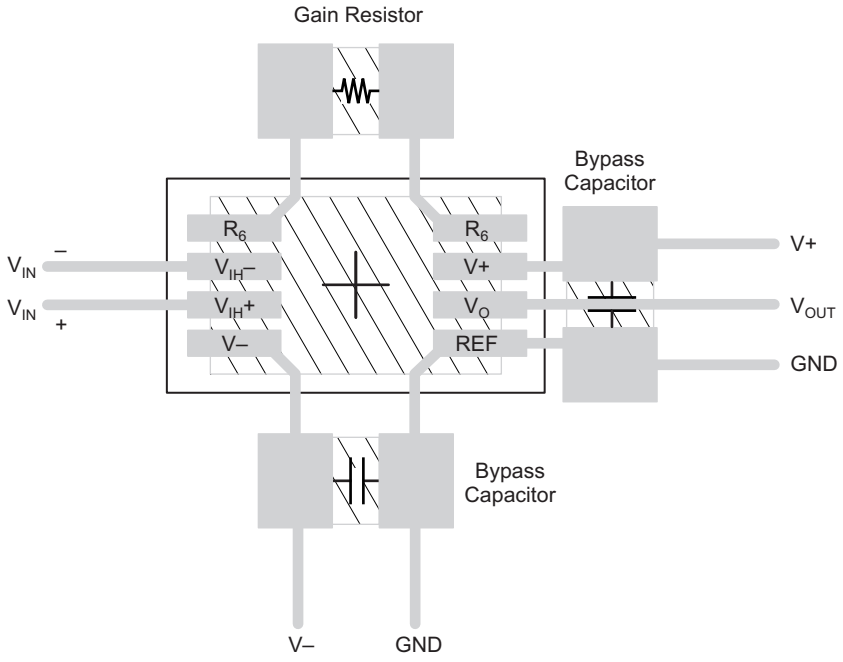


Figure 36. Recommended Layout

12 デバイスおよびドキュメントのサポート

12.1 関連リンク

表 1 に、クイック・アクセス・リンクの一覧を示します。カテゴリには、技術資料、サポートおよびコミュニティ・リソース、ツールとソフトウェア、およびサンプル注文またはご購入へのクイック・アクセスが含まれます。

表 1. 関連リンク

製品	プロダクト・フォルダ	サンプルとご購入	技術資料	ツールとソフトウェア	サポートとコミュニティ
INA128	ここをクリック	ここをクリック	ここをクリック	ここをクリック	ここをクリック
INA129	ここをクリック	ここをクリック	ここをクリック	ここをクリック	ここをクリック

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12.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

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以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
INA128P	ACTIVE	PDIP	P	8	50	Green (RoHS & no Sb/Br)	NIPDAU	N / A for Pkg Type		INA128P	Samples
INA128PA	ACTIVE	PDIP	P	8	50	Green (RoHS & no Sb/Br)	NIPDAU	N / A for Pkg Type		INA128P A	Samples
INA128PG4	ACTIVE	PDIP	P	8	50	Green (RoHS & no Sb/Br)	NIPDAU	N / A for Pkg Type		INA128P	Samples
INA128U	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR		INA 128U	Samples
INA128U/2K5	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR		INA 128U	Samples
INA128U/2K5G4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR		INA 128U	Samples
INA128UA	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR	-40 to 125	INA 128U A	Samples
INA128UA/2K5	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR	-40 to 125	INA 128U A	Samples
INA128UA/2K5E4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR	-40 to 125	INA 128U A	Samples
INA128UA/2K5G4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR	-40 to 125	INA 128U A	Samples
INA128UAE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR	-40 to 125	INA 128U A	Samples
INA128UAG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR	-40 to 125	INA 128U A	Samples
INA128UG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR		INA 128U	Samples
INA129P	ACTIVE	PDIP	P	8	50	Green (RoHS & no Sb/Br)	NIPDAU	N / A for Pkg Type		INA129P	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
INA129PA	ACTIVE	PDIP	P	8	50	Green (RoHS & no Sb/Br)	NIPDAU	N / A for Pkg Type		INA129P A	Samples
INA129PG4	ACTIVE	PDIP	P	8	50	Green (RoHS & no Sb/Br)	NIPDAU	N / A for Pkg Type		INA129P	Samples
INA129U	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR		INA 129U	Samples
INA129U/2K5	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR		INA 129U	Samples
INA129UA	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR	-40 to 125	INA 129U A	Samples
INA129UA/2K5	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR	-40 to 125	INA 129U A	Samples
INA129UA/2K5G4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR	-40 to 125	INA 129U A	Samples
INA129UAE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR	-40 to 125	INA 129U A	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

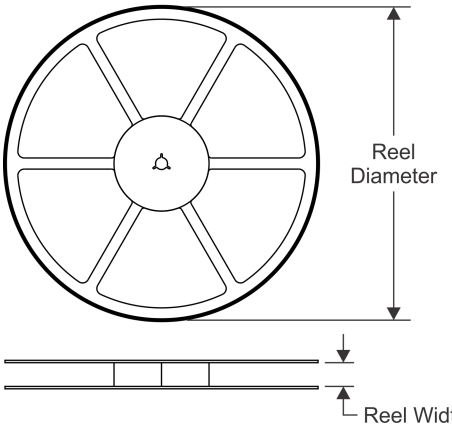
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

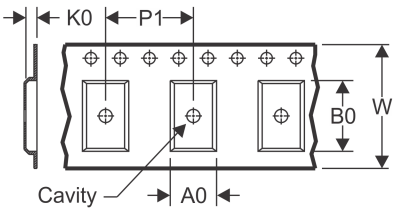
(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

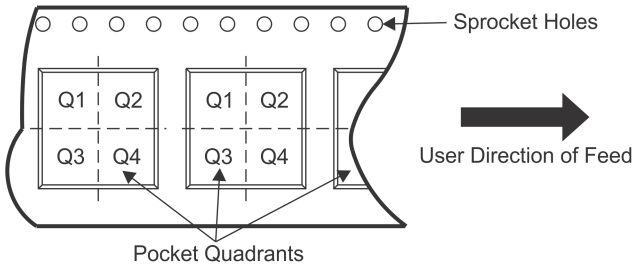


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

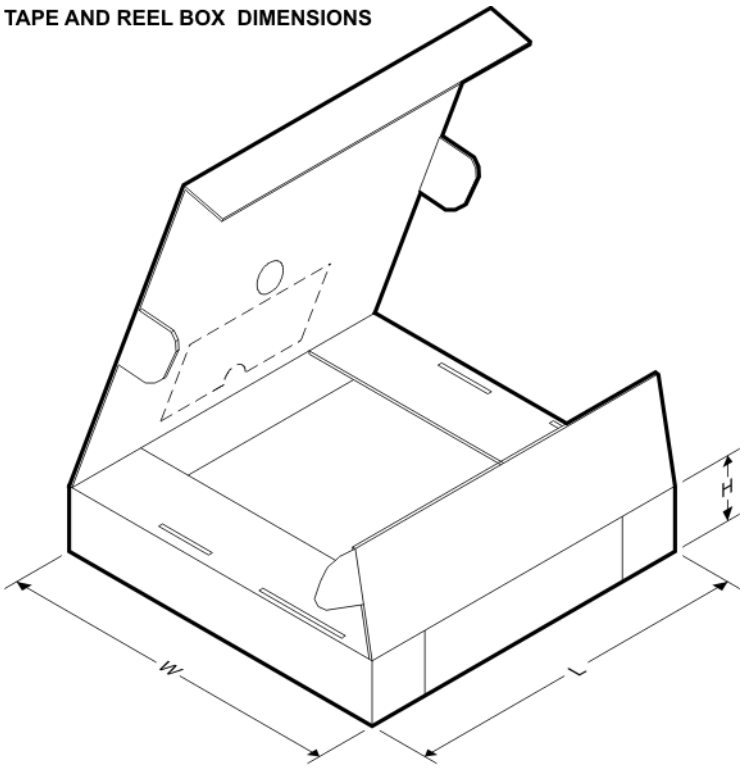
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

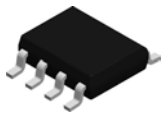
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA128U/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
INA128UA/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
INA129U/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
INA129UA/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
INA128U/2K5	SOIC	D	8	2500	367.0	367.0	35.0
INA128UA/2K5	SOIC	D	8	2500	367.0	367.0	35.0
INA129U/2K5	SOIC	D	8	2500	367.0	367.0	35.0
INA129UA/2K5	SOIC	D	8	2500	367.0	367.0	35.0

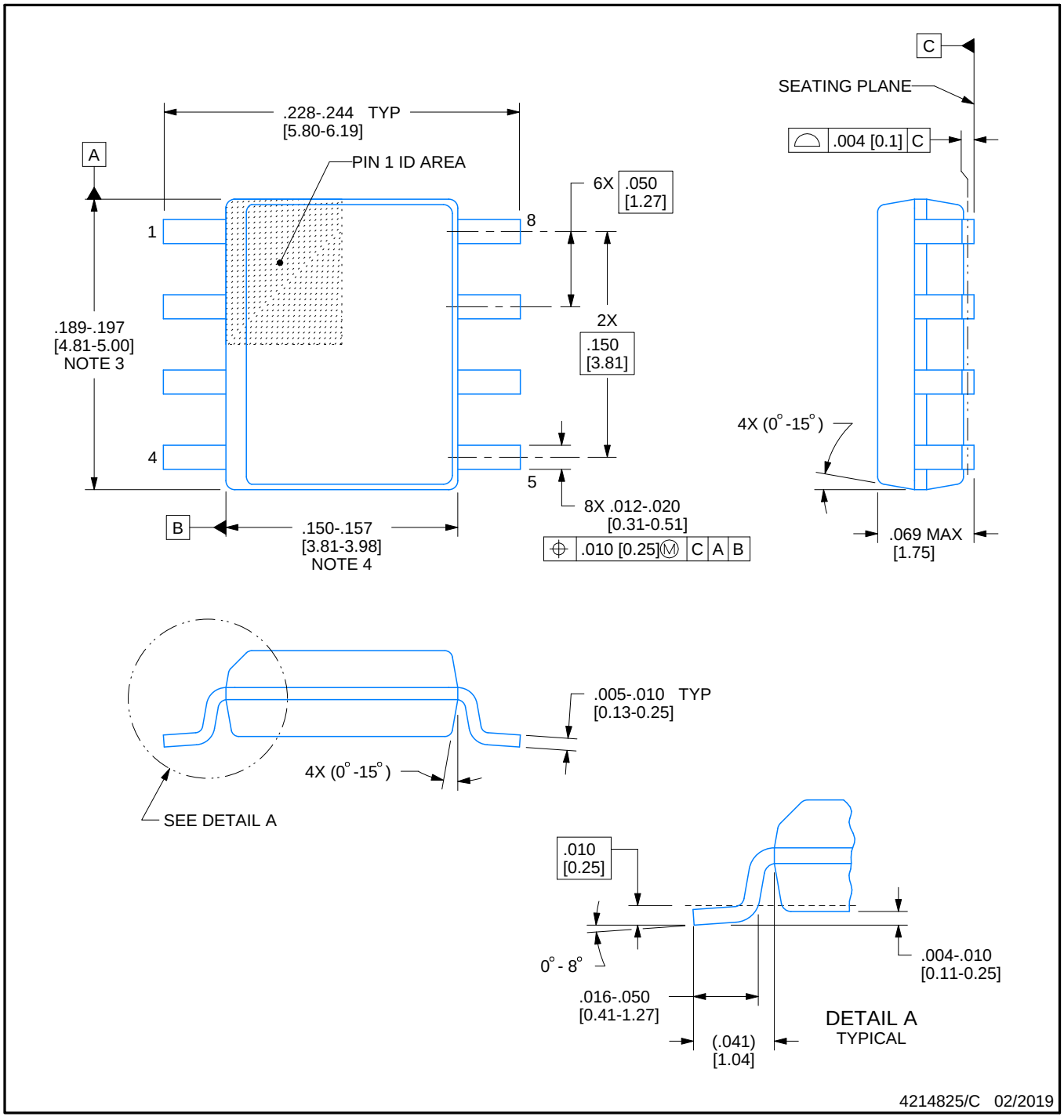


PACKAGE OUTLINE

D0008A

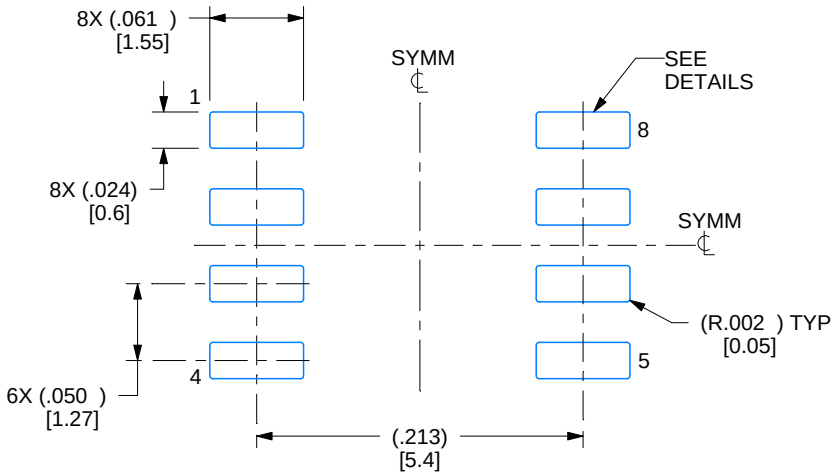
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

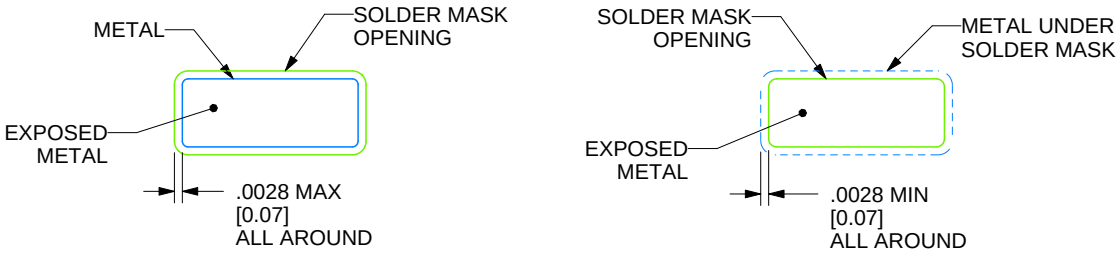


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

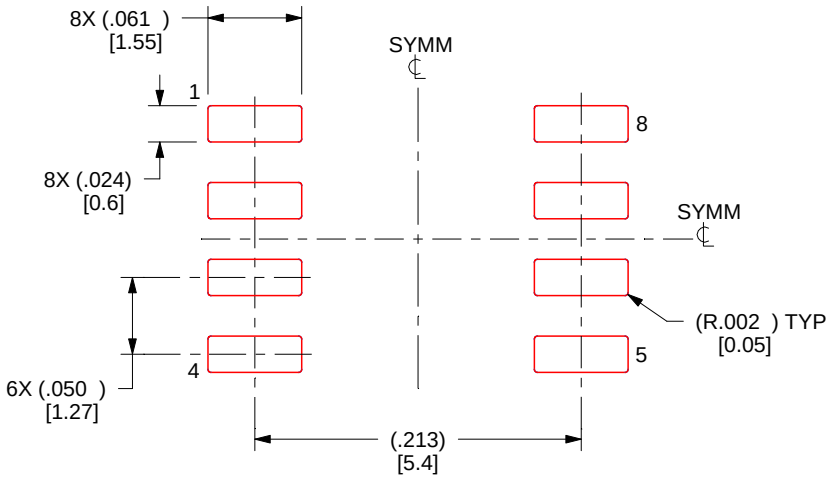
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

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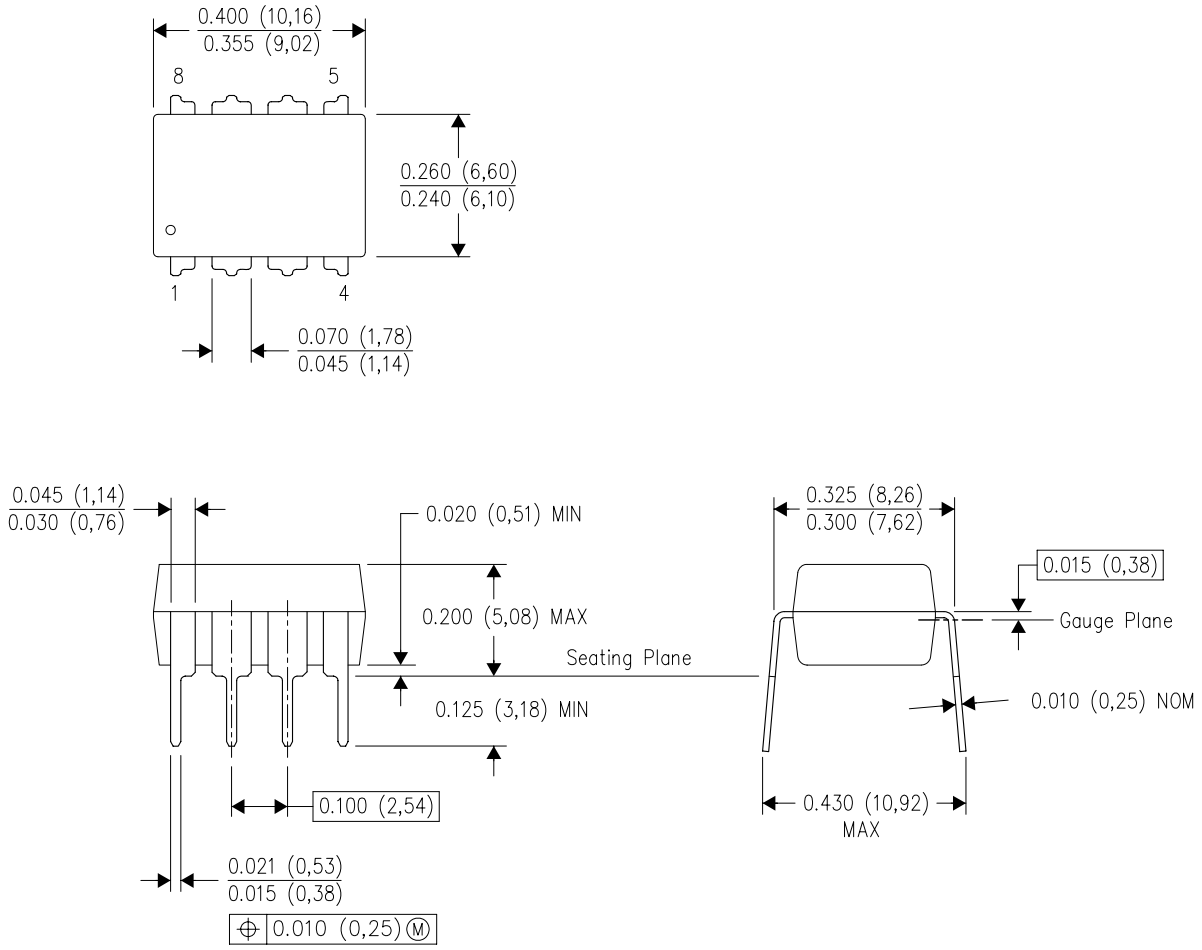
NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

P (R–PDIP–T8) PLASTIC DUAL–IN–LINE PACKAGE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS–001 variation BA.

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